

## **Description**

The BSC042N03MSG uses advanced trench technology

to provide excellent  $R_{DS(ON)}$ , low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



 $V_{DS} = 30V I_{D} = 120A$ 

 $R_{DS(ON)} < 4.4 \text{mÙ V}_{GS} = 10 \text{V}$ 

#### **Application**

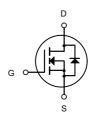
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

### **Package Marking and Ordering Information**

| Product ID   | Pack      | Marking       | Qty(PCS) |
|--------------|-----------|---------------|----------|
| BSC042N03MSG | DFN5X6-8L | 042N03MS XXXX | 5000     |

Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

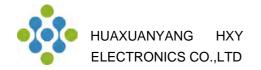
| Symbol                                | Parameter   | Rating                                   | Units |  |
|---------------------------------------|---|--|-------|--|
| Vps                                   | Drain-Source Voltage  | 30                                       | V     |  |
| Vgs                                   | Gate-Source Voltage   | ±20                                      | V     |  |
| I <sub>D</sub> @T <sub>C</sub> =25°C  | Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,6</sup>  | 120                                      | А     |  |
| I <sub>D</sub> @T <sub>C</sub> =100°C | Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,6</sup>  | 66                                       | А     |  |
| Ідм                                   | Pulsed Drain Current <sup>2</sup>                               | 320                                      | А     |  |
| EAS                                   | Single Pulse Avalanche Energy³                                  | 180                                      | mJ    |  |
| las                                   | Avalanche Current   | 60                                       | А     |  |
| P <sub>D</sub> @T <sub>C</sub> =25°C  | Total Power Dissipation <sup>4</sup>                            | Total Power Dissipation <sup>4</sup> 187 |       |  |
| Тѕтс                                  | Storage Temperature Range -55 to 150                            |  | °C    |  |
| TJ                                    | T <sub>J</sub> Operating Junction Temperature Range             |  | °C    |  |
| R <sub>θ</sub> JA                     | Thermal Resistance Junction-Ambient <sup>1</sup> 62             |  | °C/W  |  |
| Rejc                                  | R <sub>θ</sub> JC Thermal Resistance Junction-Case <sup>1</sup> |  | °C/W  |  |



### N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

| Symbol                        | Parameter Conditions                           |   | Min. | Тур.  | Max. | Unit               |
|-------------------------------|--|---|------|-------|------|--------------------|
| BV <sub>DSS</sub>             | Drain-Source Breakdown Voltage                 | V <sub>GS</sub> =0V , I <sub>D</sub> =250uA                       | 30   |       |      | V                  |
| 2BVoss/2TJ                    | BV <sub>DSS</sub> Temperature Coefficient      | Reference to 25°C , I <sub>D</sub> =1mA                           |      | 0.014 |      | V/°C               |
|                               |  | V <sub>GS</sub> =10V , I <sub>D</sub> =30A                        |      | 3.5   | 4.4  |                    |
| RDS(ON)                       | Static Drain-Source On-Resistance <sup>2</sup> | V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A                       |      | 4.6   | 5.8  | $\mathbf{m}\Omega$ |
| V <sub>GS(th)</sub>           | Gate Threshold Voltage                         |   | 1.2  |       | 2.5  | V                  |
| $\mathbb{P}V_{\text{GS(th)}}$ | V <sub>GS(th)</sub> Temperature Coefficient    | <br>V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA      |      | -4    |      | mV/°C              |
| Ipss                          | Drain-Source Leakage Current                   | V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C |      |       | 1    |                    |
|                               |  | V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C |      |       | 5    | uA                 |
| Igss                          | Gate-Source Leakage Current                    | V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V                       |      |       | ±100 | nA                 |
| gfs                           | Forward Transconductance                       | V <sub>DS</sub> =5V , I <sub>D</sub> =30A                         |      | 50    |      | S                  |
| Rg                            | Gate Resistance                                | V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz                |      | 1.7   |      | Ω                  |
| Qg                            | Total Gate Charge (4.5V)                       |   |      | 56.9  |      |                    |
| Qgs                           | Gate-Source Charge                             | V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =15A |      | 13.8  |      | nC                 |
| Qgd                           | Gate-Drain Charge                              |   |      | 23.5  |      |                    |
| Td(on)                        | Turn-On Delay Time                             |   |      | 20.1  |      |                    |
| Tr                            | Rise Time                                      | V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,                     |      | 6.3   |      |                    |
| Td(off)                       | Turn-Off Delay Time                            | —R <sub>G</sub> =3.3 ,<br>I <sub>D</sub> =1A                      |      | 124.6 |      | ns                 |
| T <sub>f</sub>                | Fall Time                                      |   |      | 15.8  |      |                    |
| Ciss                          | Input Capacitance                              |   |      | 4345  |      |                    |
| Coss                          | Output Capacitance                             | V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz               |      | 340   |      | pF                 |
| Crss                          | Reverse Transfer Capacitance                   | 1   |      | 225   |      |                    |
| Is                            | Continuous Source Current <sup>1,6</sup>       | V <sub>G</sub> =V <sub>D</sub> =0V , Force Current                |      |       | 85   | Α                  |
| VsD                           | Diode Forward Voltage <sup>2</sup>             | V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C   |      |       | 1.2  | V                  |
|                               |  |   | 1    |       |      |                    |



#### **Typical Characteristics**

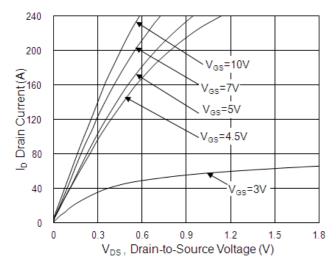


Fig.1 Typical Output Characteristics

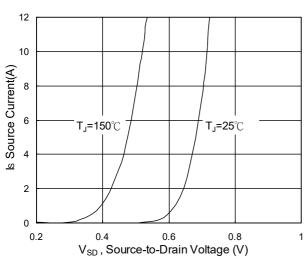


Fig.3 Forward Characteristics of Reverse

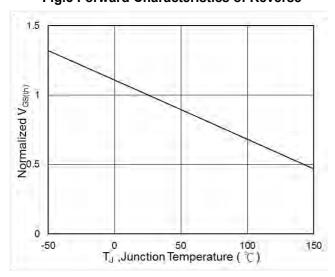


Fig.5 Normalized  $V_{\text{GS(th)}}$  v.s  $T_{\text{J}}$ 

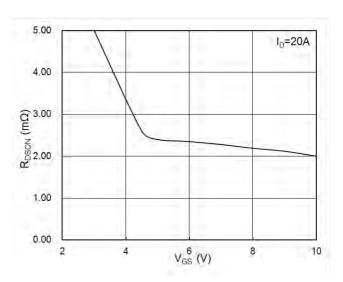


Fig.2 On-Resistance v.s Gate-Source

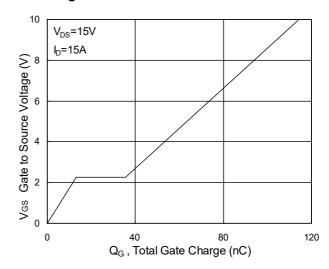


Fig.4 Gate-Charge Characteristics

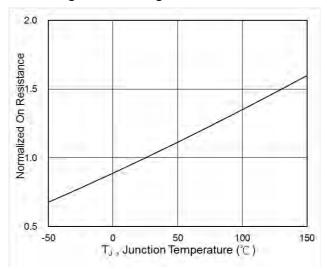


Fig.6 Normalized R<sub>DSON</sub> v.s T<sub>J</sub>

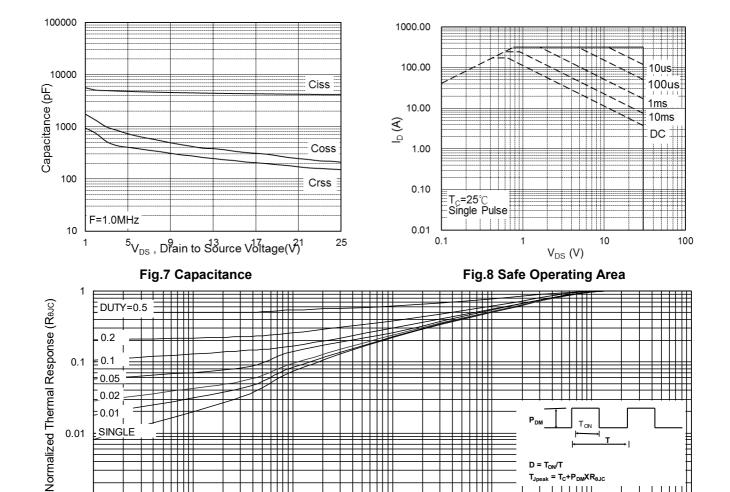
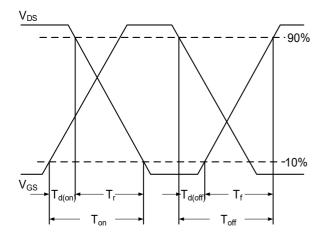


Fig.9 Normalized Maximum Transient Thermal Impedance

t, Pulse Width (s)

0.001



0.0001

0.0001

Fig.10 Switching Time Waveform

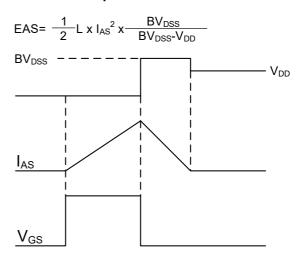
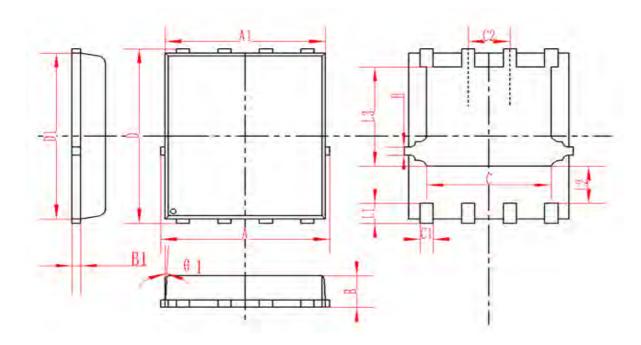


Fig.11 Unclamped Inductive Switching Waveform

## N-Channel Enhancement Mode MOSFET

## **DFN5X6-8L Package Information**



| SYMBOL | MM       |      | INCH     |       |       |       |  |
|--------|----------|------|----------|-------|-------|-------|--|
|        | MIN      | NOM  | MAX      | MIN   | NOM   | MAX   |  |
| А      | 4.95     | 5    | 5.05     | 0.195 | 0.197 | 0.199 |  |
| A1     | 4.82     | 4.9  | 4.98     | 0.190 | 0.193 | 0.196 |  |
| D      | 5.98     | 6    | 6.02     | 0.235 | 0.236 | 0.237 |  |
| D1     | 5.67     | 5.75 | 5.83     | 0.223 | 0.226 | 0.230 |  |
| В      | 0.9      | 0.95 | 1        | 0.035 | 0.037 | 0.039 |  |
| B1     | 0.254REF |      | 0.010REF |       |       |       |  |
| С      | 3.95     | 4    | 4.05     | 0.156 | 0.157 | 0.159 |  |
| C1     | 0.35     | 0.4  | 0.45     | 0.014 | 0.016 | 0.018 |  |
| C2     | 1.27TYP  |      | 0.5TYP   |       |       |       |  |
| θ1     | 8°       | 10°  | 12°      | 8°    | 10°   | 12°   |  |
| L1     | 0.63     | 0.64 | 0.65     | 0.025 | 0.025 | 0.026 |  |
| L2     | 1.2      | 1.3  | 1.4      | 0.047 | 0.051 | 0.055 |  |
| L3     | 3.415    | 3.42 | 3.425    | 0.134 | 0.135 | 0.135 |  |
| Н      | 0.24     | 0.25 | 0.26     | 0.009 | 0.010 | 0.010 |  |



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